

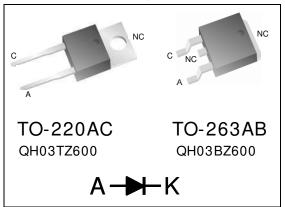
QH03TZ600, QH03BZ600 Qspeed[™] Family

600 V, 3 A H-Series PFC Diode

Product Summary

I _{F(AVG)}	3	Α
V_{RRM}	600	V
Q _{RR} (Typ at 125 °C)	14.8	nC
I _{RRM} (Typ at 125 °C)	1.35	Α
Softness t _B /t _A (Typ at 125 °C)	1.1	

Pin Assignment



RoHS Compliant

Package uses Lead-free plating and Green mold compound. Halogen free per IEC 61249-2-21.

General Description

This device has the lowest Q_{RR} of any 600 V silicon diode. Its recovery characteristics increase efficiency, reduce EMI and eliminate snubbers.

Applications

- Power Factor Correction (PFC) boost diode
- Motor drive circuits
- DC-AC Inverters

Features

- Low QRR, low IRRM, low tRR
- High dl_F/dt capable (1000 A / μs)
- Soft recovery

Benefits

- · Increases efficiency
 - Eliminates need for snubber circuits
 - Reduces EMI filter component size & count
- Enables extremely fast switching

Absolute Maximum Ratings

Absolute maximum ratings are the values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Symbol	Parameter	Conditions	Rating	Units
V_{RRM}	Peak repetitive reverse voltage	T _J = 25 °C	600	V
I _{F(AVG)}	Average forward current	T _J = 150 °C, T _C = 120 °C	3	Α
I _{FSM}	Non-repetitive peak surge current	60 Hz, $\frac{1}{2}$ cycle, $T_C = 25 ^{\circ}\text{C}$	35	Α
I _{FSM}	Non-repetitive peak surge current	$1/_{2}$ cycle of t = 28 μs Sinusoid, T_{C} = 25 °C	350	Α
TJ	Operating junction temperature range		-55 to 150	°C
T _{STG}	Storage temperature		-55 to 150	°C
	Lead soldering temperature	Leads at 1.6 mm from case, 10 sec	300	°C
V_{ISOL}	Isolation voltage (leads-to-tab)	AC, TO-220	2500	٧
V_{ISOL}	Isolation voltage (leads-to-tab)	AC, TO-263	1500	V
P_D	Power dissipation	T _C = 25 °C	30.4	W

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Thermal Resistance

Symbol	Resistance from:	Conditions	Rating	Units
$R_{\theta JA}$	Junction to ambient	TO-220 (only)	62	°C/W
$R_{\theta JC}$	Junction to case		4.1	°C/W

Electrical Specifications at $T_{ij} = 25$ °C (unless otherwise specified)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
DC Chara	DC Characteristics						
ı	Povorgo gurront	V _R = 600 V, T _J = 25 °C		-	-	250	μА
I _R	Reverse current	$V_R = 600 \text{ V}, T_J = 125$	600 V, T _J = 125 °C		0.22	-	mA
M	Forward voltage	I _F = 3 A, T _J = 25 °C		1	2.52	3.0	V
V_{F}	Forward voltage	$I_F = 3 \text{ A}, T_J = 150 ^{\circ}\text{C}$		-	2.1	-	V
CJ	Junction capacitance	$V_R = 10 \text{ V}, 1 \text{ MHz}$		-	11	-	рF
Dynamic	Characteristics						
+	Dovorgo rogovory timo	$dI/dt = 200 A/\mu s$	$T_J = 25 ^{\circ}C$	-	9.8	-	ns
t _{RR}	Reverse recovery time	$V_R = 400 \text{ V}, I_F = 3 \text{ A}$	T _J = 125 °C	-	16.1	-	ns
0	Reverse recovery	$dI/dt = 200 A/\mu s$	$T_J = 25 ^{\circ}C$	-	5.8	10	nC
Q_{RR}	charge	$V_R = 400 \text{ V}, I_F = 3 \text{ A}$	T _J = 125 °C	1	14.8	-	nC
	Maximum reverse	$dI/dt = 200 A/\mu s$	T _J = 25 °C	1	0.93	1.4	Α
I _{RRM}	recovery current	$V_R = 400 \text{ V}, I_F = 3 \text{ A}$	T _J = 125 °C	-	1.35	-	Α
	Softness factor = $\frac{t_B}{}$		$T_J = 25 ^{\circ}C$	-	0.92	-	
S Sc	Somess factor = $\frac{S}{t_A}$		T _J = 125 °C	-	1.1	-	

Note to component engineers: H-Series diodes employ Schottky technologies in their design and construction. Therefore, Component Engineers should plan their test setups to be similar to those for traditional Schottky test setups. (For additional details, see Application Note AN-300.)

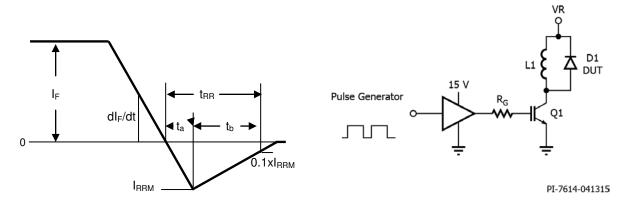
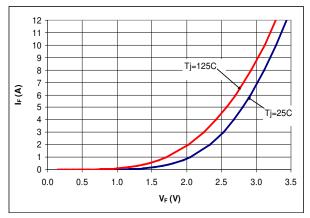


Figure 1. Reverse Recovery Definitions.

Figure 2. Reverse Recovery Test Circuit.

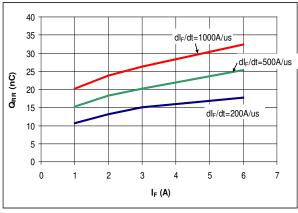
Electrical Specifications at $T_J = 25$ °C (unless otherwise specified)



35 30 25 20 0 15 10 0 20 40 60 80 100 120 140 160 180 V_R(V)

Figure 3. Typical I_F vs. V_F.

Figure 4. Typical C_J vs V_R.



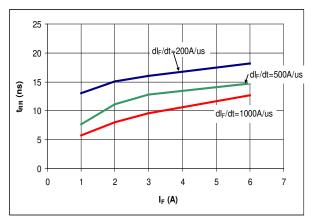
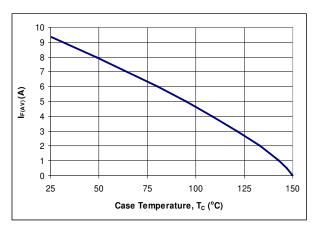


Figure 5. Typical Q_{RR} vs. I_F at T_J = 125 °C.

Figure 6. Typical t_{RR} vs. I_F at T_J = 125 °C.



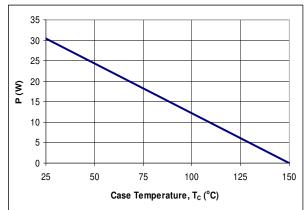


Figure 7. DC Current Derating Curve.

Figure 8. Power Derating Curve.

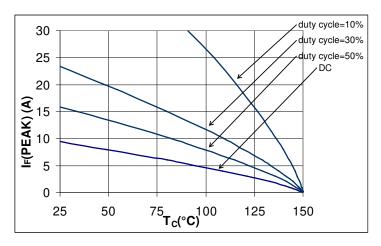


Figure 9. $I_F(PEAK)$ vs. T_C , f = 70 kHz.

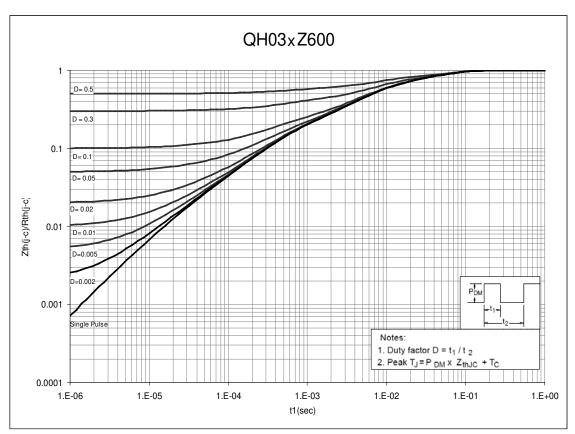
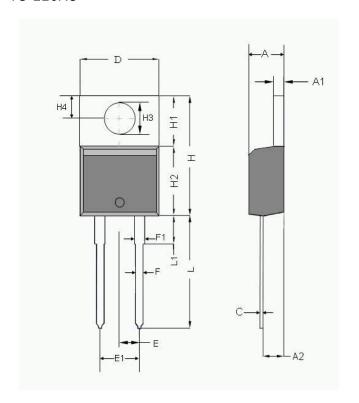


Figure 10. Normalized Maximum Transient Thermal Impedance.

Dimensional Outline Drawing

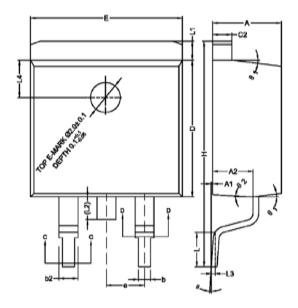
TO-220AC



	Millimeters		
Dim	MIN	MAX	
Α	4.32	4.70	
A1	1.14	1.40	
A2	2.03	2.79	
С	0.34	0.610	
D	9.65	10.67	
Е	2.49	2.59	
E1	4.98	5.18	
F	0.508	1.016	
F1	1.14	1.78	
Н	14.71	16.51	
H1	5.84	6.795	
H2	8.40	9.00	
Н3	3.53	3.96	
H4	2.54	3.05	
L	12.70	14.22	
L1	-	6.35	

Dimensional Outline Drawing

TO-263AB



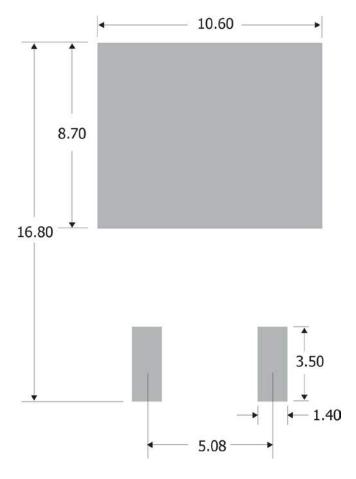
	Millimeters		
Dim	MIN	MAX	
Α	4.40	4.70	
A1	0.00	0.25	
A2	2.59	2.79	
b	0.77	0.90	
b2	1.23	1.36	
c2	1.22	1.32	
D	9.05	9.25	
Е	10.06	10.26	
е	2.54 BSC	2.54 BSC	
Н	14.70	15.50	
L	2.00	2.60	
L1	1.17	1.40	
L2	-	1.75	
L3	0.25 BSC	0.25 BSC	
L4	2.00 BSC	2.00 BSC	
Θ	0°	8°	
01	5°	9°	
Θ2	1°	5°	

Mechanical Mounting Method	Maximum Torque / Pressure specification
Screw through hole in package tab	1 Newton Meter (nm) or 8.8 inch-pounds (lb-in)
Clamp against package body	12.3 kilogram-force per square centimeter (kgf/cm²) or 175 lbf/in²

Footprint and Solder Pad Dimensions

Pad Dimensions in mm:





Soldering time and temperature: This product has been designed for use with high-temperature, lead-free solder. The component leads can be subjected to a maximum temperature of 300 °C, for up to 10 seconds. See Application Note AN-303, for more details.

Ordering Information

Part Number	Package	Packing
QH03TZ600	TO-220AB	50 units/tube
QH03BZ600	TO-263AB	800 units/reel

The information contained in this document is subject to change without notice.



QH03TZ600, QH03BZ600

Revision	Notes	Date
1.0	Released by Qspeed	01/10
1.1	Converted to Power Integrations Document	01/11
1.2	Added QH03BZ600	02/13
1.3	Updated with new Brand Style. Added footprint and solder pad dimension for TO-263AB package.	11/15



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Power Integrations Worldwide Sales Support Locations

WORLD HEADQUARTERS 5245 Hellyer Avenue San Jose, CA 95138, USA. Main: +1-408-414-9200 Customer Service: Phone: +1-408-414-9665 Fax: +1-408-414-9765 e-mail: usasales@power.com

CHINA (SHANGHAI) Rm 2410, Charity Plaza, No. 88, North Caoxi Road, Shanghai, PRC 200030 Phone: +86-21-6354-6323 Fax: +86-21-6354-6325 e-mail: chinasales@power.com

CHINA (SHENZHEN) 17/F, Hivac Building, No. 2, Keji Nan 8th Road, Nanshan District, Shenzhen, China, 518057 Phone: +86-755-8672-8689 Fax: +86-755-8672-8690 e-mail: chinasales@power.com

GERMANY Lindwurmstrasse 114 80337, Munich Germany Phone: +49-895-527-39110

Fax: +49-895-527-39200 e-mail: eurosales@power.com

#1, 14th Main Road Vasanthanagar Bangalore-560052

India Phone: +91-80-4113-8020 Fax: +91-80-4113-8023

indiasales@power.com

e-mail:

I TAI Y Via Milanese 20, 3rd. Fl. 20099 Sesto San Giovanni (MI) Italy

Phone: +39-024-550-8701 Fax: +39-028-928-6009

eurosales@power.com

JAPAN Kosei Dai-3 Building 2-12-11, Shin-Yokohama, Kohoku-ku Yokohama-shi, Kanagawa 222-0033 Japan Phone: +81-45-471-1021

Fax: +81-45-471-3717

RM 602, 6FL Korea City Air Terminal B/D, 159-6 Samsung-Dong, Kangnam-Gu, Seoul. 135-728 Korea

e-mail: japansales@power.com

Phone: +82-2-2016-6610 Fax: +82-2-2016-6630 e-mail: koreasales@power.com

SINGAPORE 51 Newton Road, #19-01/05 Goldhill Plaza Singapore, 308900 Phone: +65-6358-2160 Fax: +65-6358-2015

TAIWAN 5F, No. 318, Nei Hu Rd., Sec. 1 Nei Hu District Taipei 11493, Taiwan R.O.C.

Phone: +886-2-2659-4570 Fax: +886-2-2659-4550 e-mail:

taiwansales@power.com

Cambridge Semiconductor, a Power Integrations company Westbrook Centre, Block 5. 2nd Floor Milton Road Cambridge CB4 1YG

Phone: +44 (0) 1223-446483 e-mail: eurosales@power.com

e-mail:

singaporesales@power.com